优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Feature

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

Feature

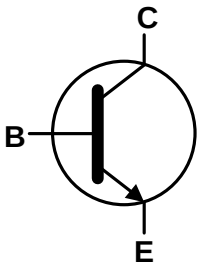
- BV_{CEO} > 120V
- I_C = 1A Continuous Collector Current
- I_{CM} = 2A Peak Pulse Current
- 500mW Power Dissipation
- h_{FE} characterised up to 1A for high current gain hold up

Mechanical Data

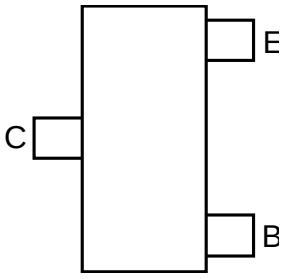
- Case: SOT23 (Type DN)
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (Approximate)

SOT23 (Type DN)

Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	140	V
Collector-Emitter Voltage	V_{CEO}	120	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	I_C	1	A
Peak Pulse Current	I_{CM}	2	A
Base Current	I_B	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

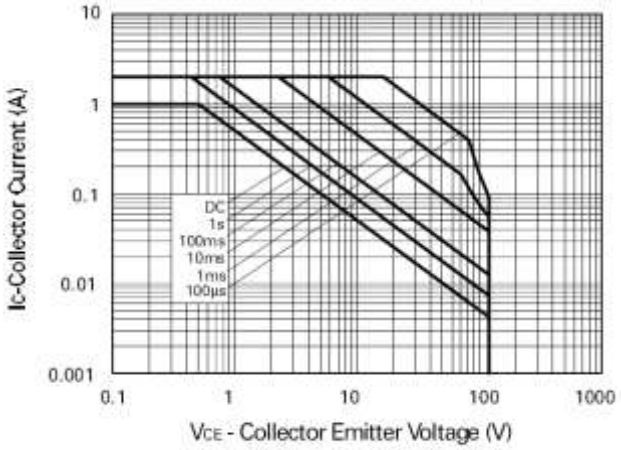
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P_D	500	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	250	°C/W
Thermal Resistance, Junction to Lead (Note 7)	$R_{\theta JL}$	197	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 8)

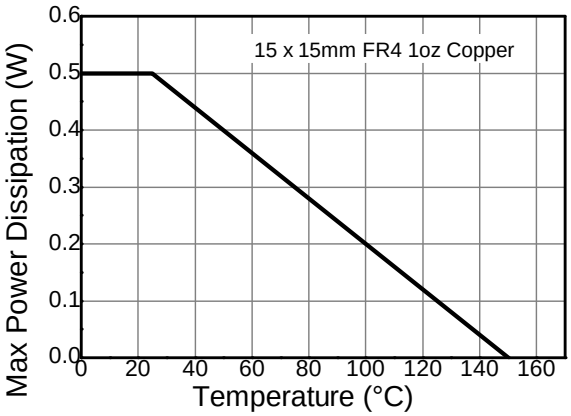
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	C

Notes:
6. For a device surface mounted on 15mm X 15mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
7. Thermal resistance from junction to solder-point (at the end of the collector lead).
8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

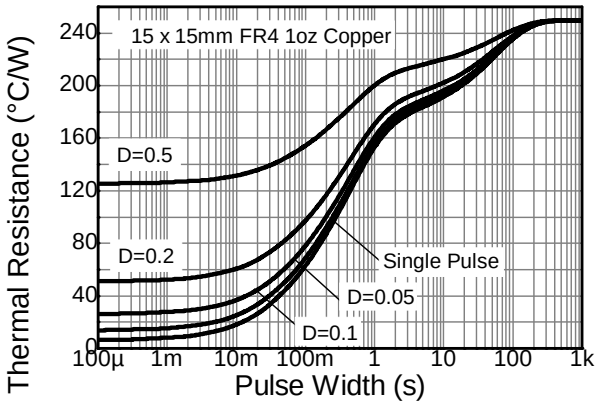
Thermal Characteristics and Derating Information



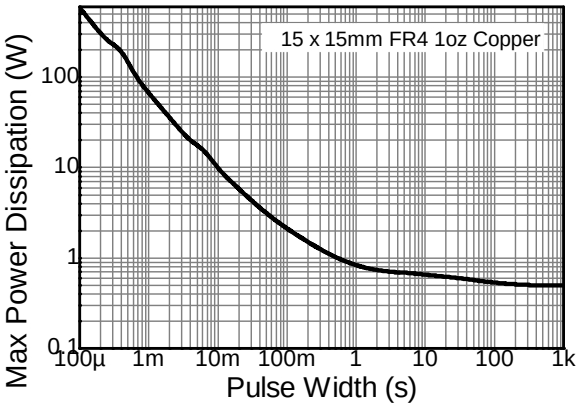
Safe Operating Area



Derating Curve



Transient Thermal Impedance



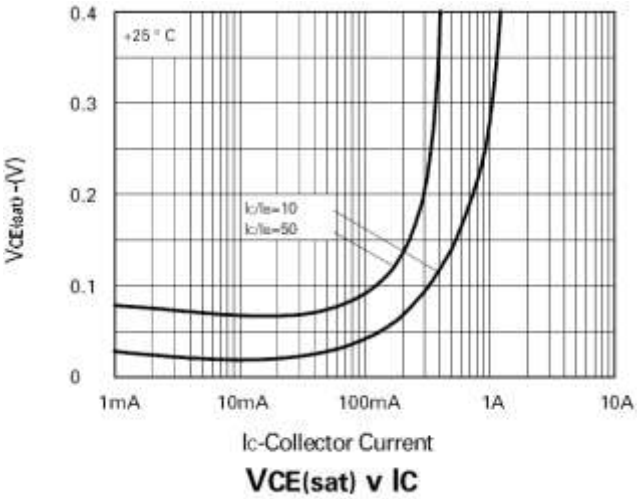
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

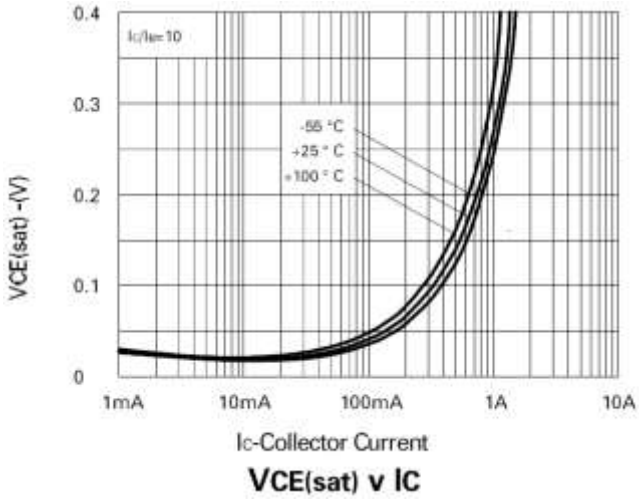
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	140	—	—	V	I_C = 100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV_{CEO}	120	—	—	V	I_C = 1mA
Emitter-Base Breakdown Voltage	BV_{EBO}	7	—	—	V	I_E = 100μA
Collector Cutoff Current	I_{CBO}	—	—	100	nA	V_{CB} = 120V
Emitter Cutoff Current	I_{EBO}	—	—	100	nA	V_{EB} = 5V
Collector Emitter Cutoff Current	I_{CES}	—	—	100	nA	V_{CE} = 120V
Static Forward Current Transfer Ratio (Note 9)	h_{FE}	100	—	—	—	I_C = 1mA, V_{CE} = 10V
		100	—	300		I_C = 250mA, V_{CE} = 10V
		60	—	—		I_C = 500mA, V_{CE} = 10V
		20	—	—		I_C = 1A, V_{CE} = 10V
Collector-Emitter Saturation Voltage (Note 9)	$V_{CE(sat)}$	—	—	200	mV	I_C = 250mA, I_B = 25mA
		—	—	300		I_C = 500mA, I_B = 50mA
Base-Emitter Turn-On Voltage(Note 9)	$V_{BE(on)}$	—	—	1.0	V	I_C = 500mA, V_{CE} = 10V
Base-Emitter Saturation Voltage(Note 9)	$V_{BE(sat)}$	—	—	1.1	V	I_C = 500mA, I_B = 50mA
Output Capacitance	C_{obo}	—	—	10	pF	V_{CB} = 10V, f = 1MHz
Transition Frequency	f_T	100	—	—	MHz	V_{CE} = 50V, I_C = 10mA, f = 100MHz

Note: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

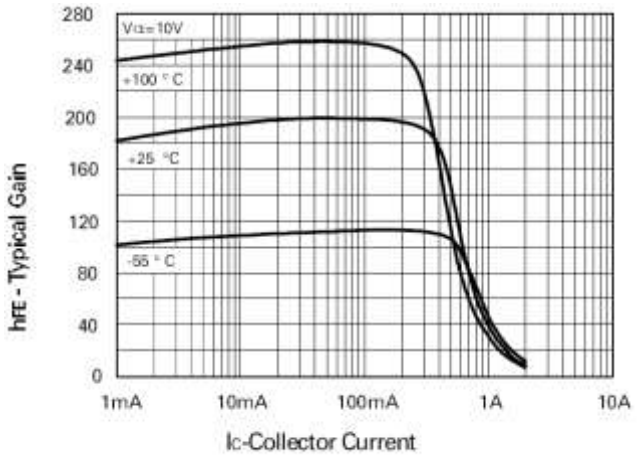
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



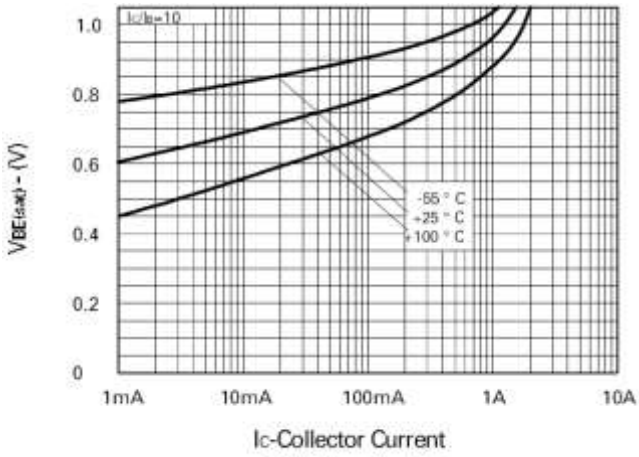
VCE(sat) v IC



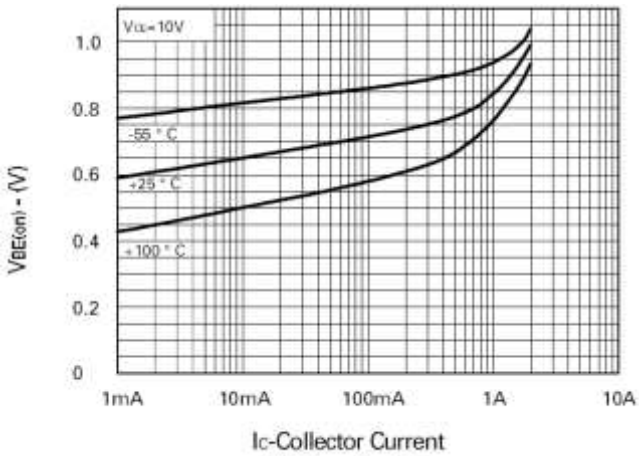
VCE(sat) v IC



hFE V IC



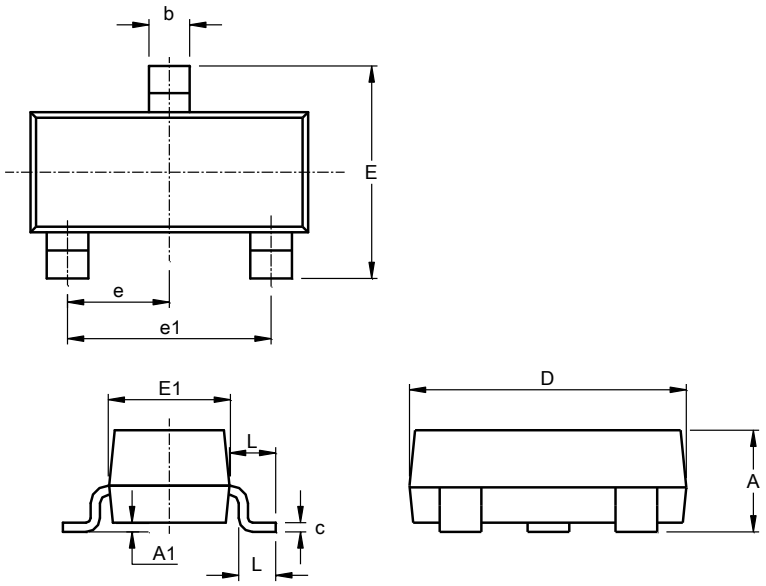
VBE(sat) v IC



VBE(on) v IC

Package Outline Dimensions

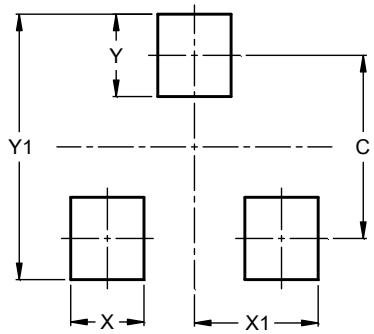
SOT23 Type DN



SOT23 Type DN			
Dim	**Min**	**Max**	**Typ**
A	0.89	1.12	1.00
A1	0.01	0.10	0.05
b	0.30	0.51	0.45
c	0.08	0.20	0.10
D	2.80	3.04	3.00
E	2.10	2.64	2.42
E1	1.20	1.40	1.37
e	0.95 REF		
e1	1.90 REF		
L	0.25	0.60	0.30
L1	0.45	0.62	0.54
All Dimensions in mm			

Suggested Pad Layout

SOT23 Type DN



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9